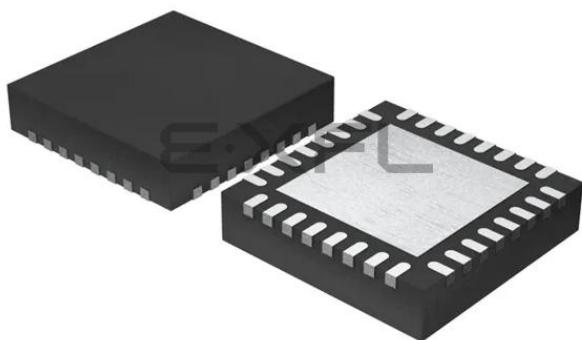




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, LINbus, SPI, UART/USART, USB, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LVD, POR, PWM, WDT
Number of I/O	23
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 7x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount, Wettable Flank
Package / Case	32-VFQFN Exposed Pad
Supplier Device Package	32-HVQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl25z64vfm4

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Terminology and guidelines

Field	Description	Values
R	Silicon revision	• (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = -40 to 105
PP	Package identifier	• FM = 32 QFN (5 mm x 5 mm) • FT = 48 QFN (7 mm x 7 mm) • LH = 64 LQFP (10 mm x 10 mm) • LK = 80 LQFP (12 mm x 12 mm)
CC	Maximum CPU frequency (MHz)	• 4 = 48 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

2.4 Example

This is an example part number:

MKL25Z64VLK4

3 Terminology and guidelines

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.1.1 Example

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

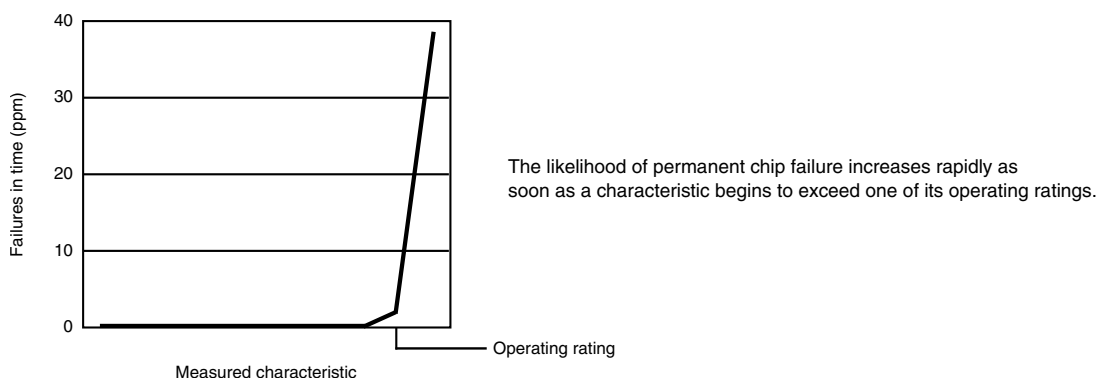
Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	0.9	1.1	V

3.4.1 Example

This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	-0.3	1.2	V

3.5 Result of exceeding a rating



3.6 Relationship between ratings and operating requirements

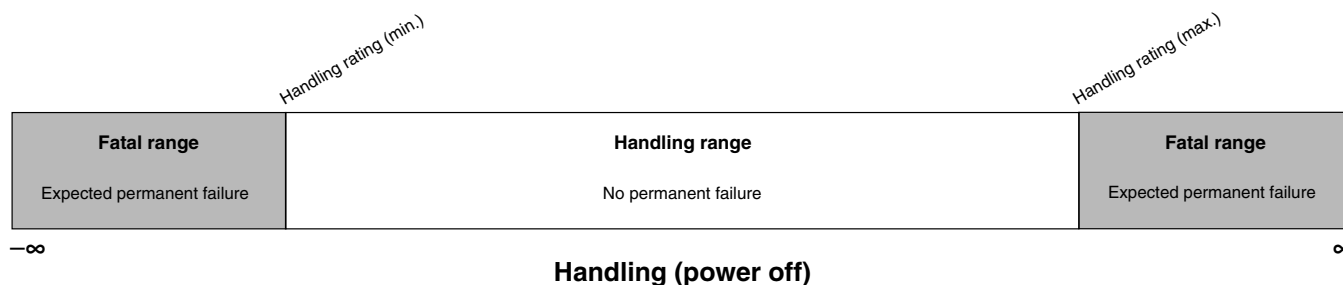
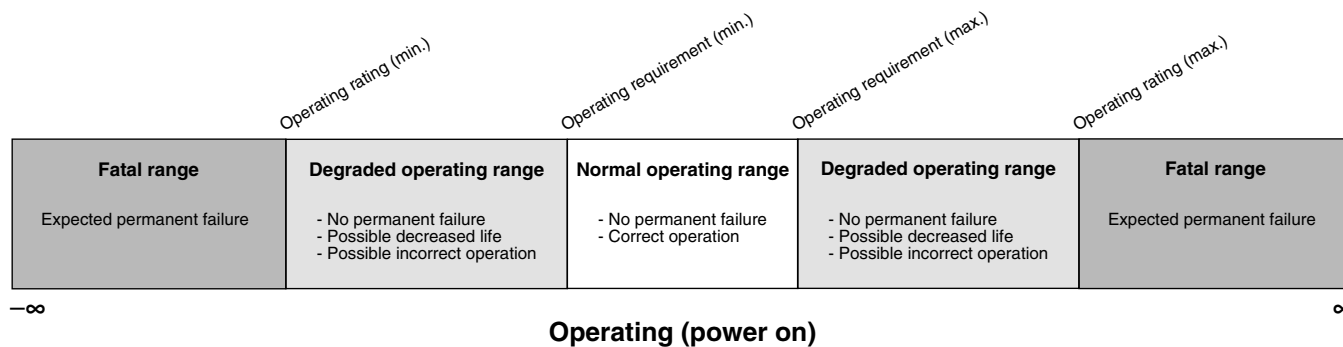


Table 2. V_{DD} supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{LVW1L}	Low-voltage warning thresholds — low range					1
	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V _{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V _{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V _{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V _{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±40	—	mV	
V _{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t _{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising thresholds are falling threshold + hysteresis voltage

5.2.3 Voltage and current operating behaviors

Table 3. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{OH}	Output high voltage — Normal drive pad				1
	• 2.7 V ≤ V _{DD} ≤ 3.6 V, I _{OH} = -5 mA	V _{DD} - 0.5	—	V	
	• 1.71 V ≤ V _{DD} ≤ 2.7 V, I _{OH} = -1.5 mA	V _{DD} - 0.5	—	V	
V _{OH}	Output high voltage — High drive pad				1
	• 2.7 V ≤ V _{DD} ≤ 3.6 V, I _{OH} = -18 mA	V _{DD} - 0.5	—	V	
	• 1.71 V ≤ V _{DD} ≤ 2.7 V, I _{OH} = -6 mA	V _{DD} - 0.5	—	V	
I _{OHT}	Output high current total for all ports	—	100	mA	
V _{OL}	Output low voltage — Normal drive pad				1
	• 2.7 V ≤ V _{DD} ≤ 3.6 V, I _{OL} = 5 mA	—	0.5	V	
	• 1.71 V ≤ V _{DD} ≤ 2.7 V, I _{OL} = 1.5 mA	—	0.5	V	
V _{OL}	Output low voltage — High drive pad				1
	• 2.7 V ≤ V _{DD} ≤ 3.6 V, I _{OL} = 18 mA	—	0.5	V	
	• 1.71 V ≤ V _{DD} ≤ 2.7 V, I _{OL} = 6 mA	—	0.5	V	
I _{OLT}	Output low current total for all ports	—	100	mA	
I _{IN}	Input leakage current (per pin) for full temperature range	—	1	μA	2
I _{IN}	Input leakage current (per pin) at 25 °C	—	0.025	μA	2
I _{IN}	Input leakage current (total all pins) for full temperature range	—	65	μA	2
I _{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	

Table continues on the next page...

Table 3. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Max.	Unit	Notes
R _{PU}	Internal pullup resistors	20	50	kΩ	3
R _{PD}	Internal pulldown resistors	20	50	kΩ	4

1. PTB0, PTB1, PTD6, and PTD7 I/O have both high drive and normal drive capability selected by the associated PTx_PCRn[DSE] control bit. All other GPIOs are normal drive only.
2. Measured at V_{DD} = 3.6 V
3. Measured at V_{DD} supply voltage = V_{DD} min and V_{input} = V_{SS}
4. Measured at V_{DD} supply voltage = V_{DD} min and V_{input} = V_{DD}

5.2.4 Power mode transition operating behaviors

All specifications except t_{POR} and VLLSx→RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 48 MHz
- Bus and flash clock = 24 MHz
- FEI clock mode

Table 4. Power mode transition operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t _{POR}	After a POR event, amount of time from the point V _{DD} reaches 1.8 V to execution of the first instruction across the operating temperature range of the chip.	—	—	300	μs	
	• VLLS0 → RUN	—	95	115	μs	
	• VLLS1 → RUN	—	93	115	μs	
	• VLLS3 → RUN	—	42	53	μs	
	• LLS → RUN	—	4	4.6	μs	
	• VLPS → RUN	—	4	4.4	μs	
	• STOP → RUN	—	4	4.4	μs	

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I _{DD_VLPR}	Very low power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash • at 3.0 V	—	300	745	μA	5, 4
I _{DD_VLPW}	Very low power wait mode current - core disabled / 4 MHz system / 0.8 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	—	135	496	μA	5
I _{DD_STOP}	Stop mode current at 3.0 V at 25 °C at 50 °C at 70 °C at 85 °C at 105 °C	— — — — —	345 357 392 438 551	490 827 869 927 1065	μA	
I _{DD_VLPS}	Very-low-power stop mode current at 3.0 V at 25 °C at 50 °C at 70 °C at 85 °C at 105 °C	— — — — —	4.4 10 20 37 81	16 35 50 112 201	μA	
I _{DD_LLS}	Low leakage stop mode current at 3.0 V at 25 °C at 50 °C at 70 °C at 85 °C at 105 °C	— — — — —	1.9 3.6 6.5 13 30	3.7 39 43 49 69	μA	
I _{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V at 25 °C at 50 °C at 70 °C at 85 °C at 105 °C	— — — — —	1.4 2.5 5.1 9.2 21	3.2 19 21 26 38	μA	
I _{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0V at 25°C at 50°C at 70°C at 85°C at 105°C	— — — — —	0.7 1.3 2.3 5.1 13	1.4 13 14 17 25	μA	

Table continues on the next page...

Table 6. Low power mode peripheral adders — typical value (continued)

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
I _{EREFSTEN32KHz}	External 32 kHz crystal clock adder by means of the OSC0_CR[EREFSTEN and EREFSTEN] bits. Measured by entering all modes with the crystal enabled.	440	490	540	560	570	580	nA
		440	490	540	560	570	580	
	VLLS1	490	490	540	560	570	680	
	VLLS3	510	560	560	560	610	680	
	LLS	510	560	560	560	610	680	
	VLPS							
	STOP							
I _{CMP}	CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.	22	22	22	22	22	22	μA
I _{RTC}	RTC peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the RTC_CR[OSCE] bit and the RTC ALARM set for 1 minute. Includes ERCLK32K (32 kHz external crystal) power consumption.	432	357	388	475	532	810	nA
I _{UART}	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at 115200 baud rate. Includes selected clock source power consumption.							μA
	MCGIRCLK (4MHz internal reference clock)	66	66	66	66	66	66	
	OSCERCLK (4MHz external crystal)	214	237	246	254	260	268	
I _{TPM}	TPM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output compare generating 100Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents.							μA
	MCGIRCLK (4MHz internal reference clock)	86	86	86	86	86	86	
	OSCERCLK (4MHz external crystal)	235	256	265	274	280	287	
I _{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	45	45	45	45	45	45	μA

Table continues on the next page...

Table 6. Low power mode peripheral adders — typical value (continued)

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
I _{ADC}	ADC peripheral adder combining the measured values at VDD and VDDA by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	366	366	366	366	366	366	μA

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE for run mode, and BLPE for VLPR mode
- USB regulator disabled
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

Table 11. SWD full voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
J1	SWD_CLK frequency of operation Serial wire debug	0	25	MHz
J2	SWD_CLK cycle period	1/J1	—	ns
J3	SWD_CLK clock pulse width Serial wire debug	20	—	ns
J4	SWD_CLK rise and fall times	—	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	—	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	—	ns
J11	SWD_CLK high to SWD_DIO data valid	—	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	—	ns

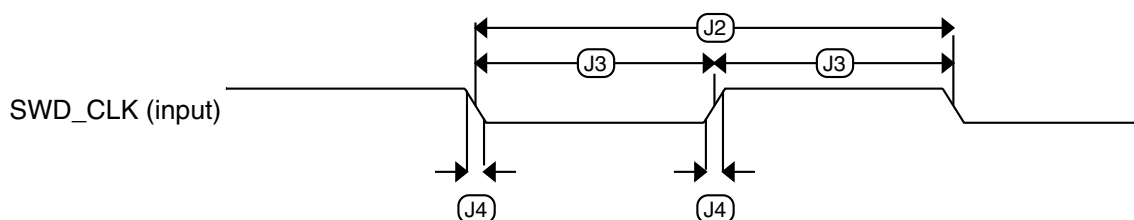
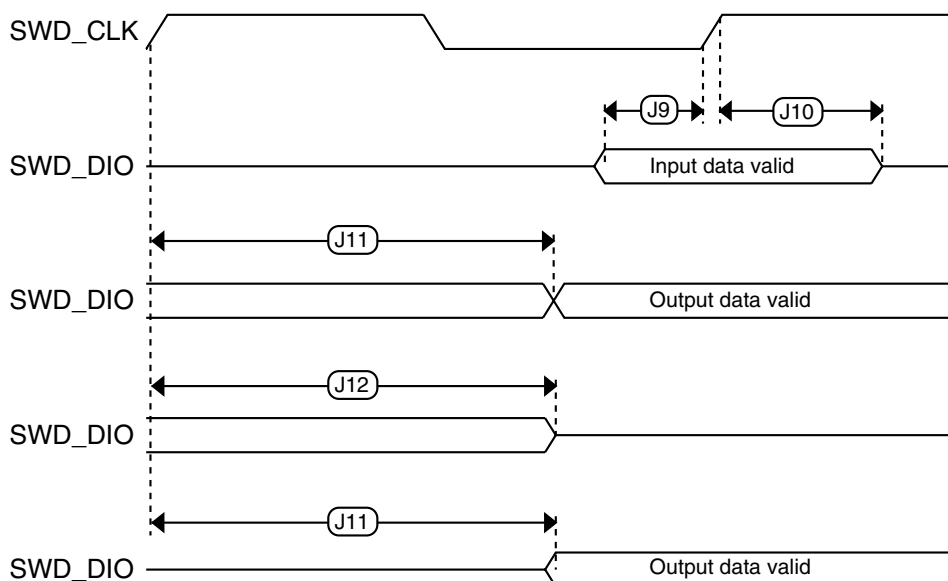
**Figure 4. Serial wire clock input timing****Figure 5. Serial wire data timing**

Table 12. MCG specifications (continued)

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
f _{dco_t_DMx32}	DCO output frequency	Low range (DRS = 00)	—	23.99	—	MHz	5, 6
		$732 \times f_{\text{fll_ref}}$					
		Mid range (DRS = 01)	—	47.97	—	MHz	
		$1464 \times f_{\text{fll_ref}}$					
J _{cyc_fll}	FLL period jitter f_{VCO} = 48 MHz		—	180	—	ps	7
t _{fll_acquire}	FLL target frequency acquisition time		—	—	1	ms	8
PLL							
f _{vco}	VCO operating frequency		48.0	—	100	MHz	
I _{pll}	PLL operating current PLL at 96 MHz (f_{osc_hi_1} = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 48)		—	1060	—	μA	9
I _{pll}	PLL operating current PLL at 48 MHz (f_{osc_hi_1} = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 24)		—	600	—	μA	9
f _{pll_ref}	PLL reference frequency range		2.0	—	4.0	MHz	
J _{cyc_pll}	PLL period jitter (RMS) - f_{VCO} = 48 MHz - f_{VCO} = 100 MHz		— —	120 50	— —	ps ps	10
J _{acc_pll}	PLL accumulated jitter over 1μs (RMS) - f_{VCO} = 48 MHz - f_{VCO} = 100 MHz		— —	1350 600	— —	ps ps	10
D _{lock}	Lock entry frequency tolerance		± 1.49	—	± 2.98	%	
D _{uni}	Lock exit frequency tolerance		± 4.47	—	± 5.97	%	
t _{pll_lock}	Lock detector detection time		—	—	150 × 10 ⁻⁶ + 1075(1/f _{pll_ref})	s	11

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. The deviation is relative to the factory trimmed frequency at nominal V_{DD} and 25 °C, $f_{\text{ints_ft}}$.
3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 0.
4. The resulting system clock frequencies must not exceed their maximum specified values. The DCO frequency deviation ($\Delta f_{\text{dco_t}}$) over voltage and temperature must be considered.
5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 1.
6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
7. This specification is based on standard deviation (RMS) of period or frequency.
8. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
9. Excludes any oscillator currents that are also consuming power while PLL is in operation.
10. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
11. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

Table 13. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
R _S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V _{pp} ⁵	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V _{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V _{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x,C_y can be provided by using the integrated capacitors when the low frequency oscillator (RANGE = 00) is used. For all other cases external capacitors must be used..
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.2.2 Oscillator frequency specifications

Table 14. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f _{osc_lo}	Oscillator crystal or resonator frequency — low frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
f _{osc_hi_1}	Oscillator crystal or resonator frequency — high frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
f _{osc_hi_2}	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f _{ec_extal}	Input clock frequency (external clock mode)	—	—	48	MHz	1, 2
t _{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	

Table continues on the next page...

6.4.1.2 Flash timing specifications — commands**Table 16. Flash command timing specifications**

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	μ s	1
t_{pgmchk}	Program Check execution time	—	—	45	μ s	1
t_{rdsrc}	Read Resource execution time	—	—	30	μ s	1
t_{pgm4}	Program Longword execution time	—	65	145	μ s	
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	
t_{rdonce}	Read Once execution time	—	—	25	μ s	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μ s	
t_{ersall}	Erase All Blocks execution time	—	62	500	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μ s	1

1. Assumes 25MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

6.4.1.3 Flash high voltage current behaviors**Table 17. Flash high voltage current behaviors**

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications**Table 18. NVM reliability specifications**

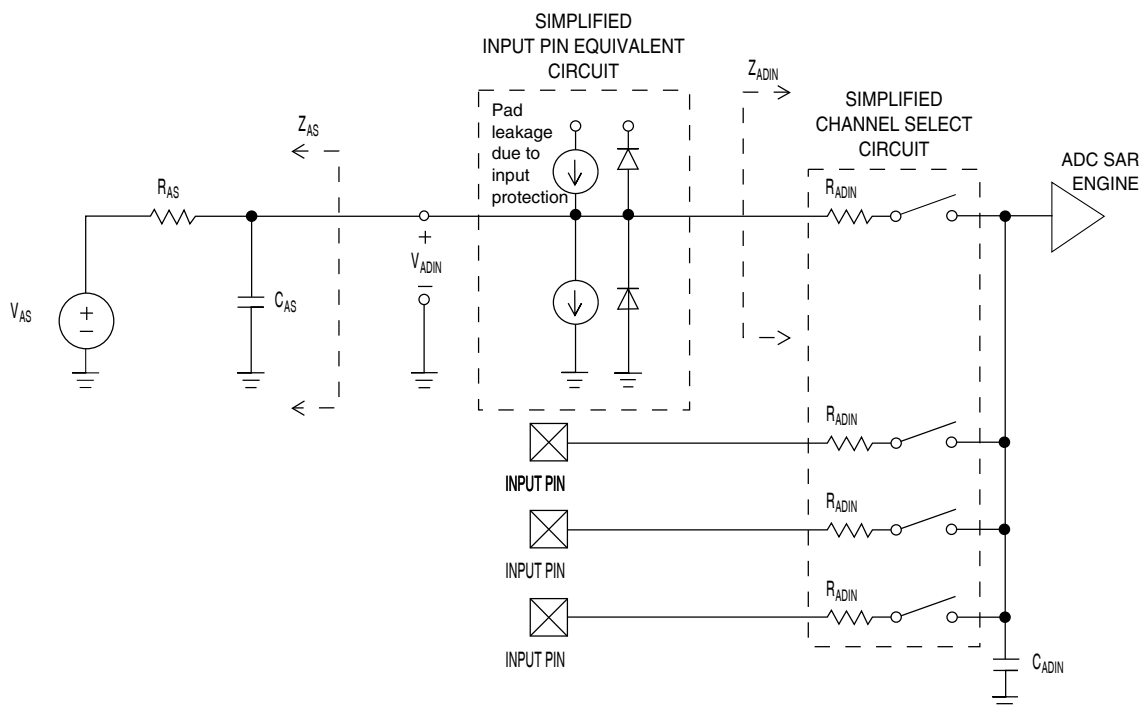
Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
Program Flash						
$t_{nv mretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nv mretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nv mcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at $-40^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$.

Table 19. 16-bit ADC operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
C_{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	Ksps	6

1. Typical values assume $V_{DDA} = 3.0\text{ V}$, $\text{Temp} = 25\text{ }^{\circ}\text{C}$, $f_{ADCK} = 1.0\text{ MHz}$ unless otherwise stated. Typical values are for reference only and are not tested in production.
2. DC potential difference.
3. For packages without dedicated VREFH and VREFL pins, V_{REFH} is internally tied to V_{DDA} , and V_{REFL} is internally tied to V_{SSA} .
4. This resistance is external to MCU. The analog source resistance must be kept as low as possible to achieve the best results. The results in this data sheet were derived from a system which has $< 8\text{ }\Omega$ analog source resistance. The R_{AS}/C_{AS} time constant should be kept to $< 1\text{ ns}$.
5. To use the maximum ADC conversion clock frequency, the ADHSC bit must be set and the ADLPC bit must be clear.
6. For guidelines and examples of conversion rate calculation, download the [ADC calculator tool](#)

**Figure 6. ADC input impedance equivalency diagram**

6.6.1.2 16-bit ADC electrical characteristics

Table 20. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3

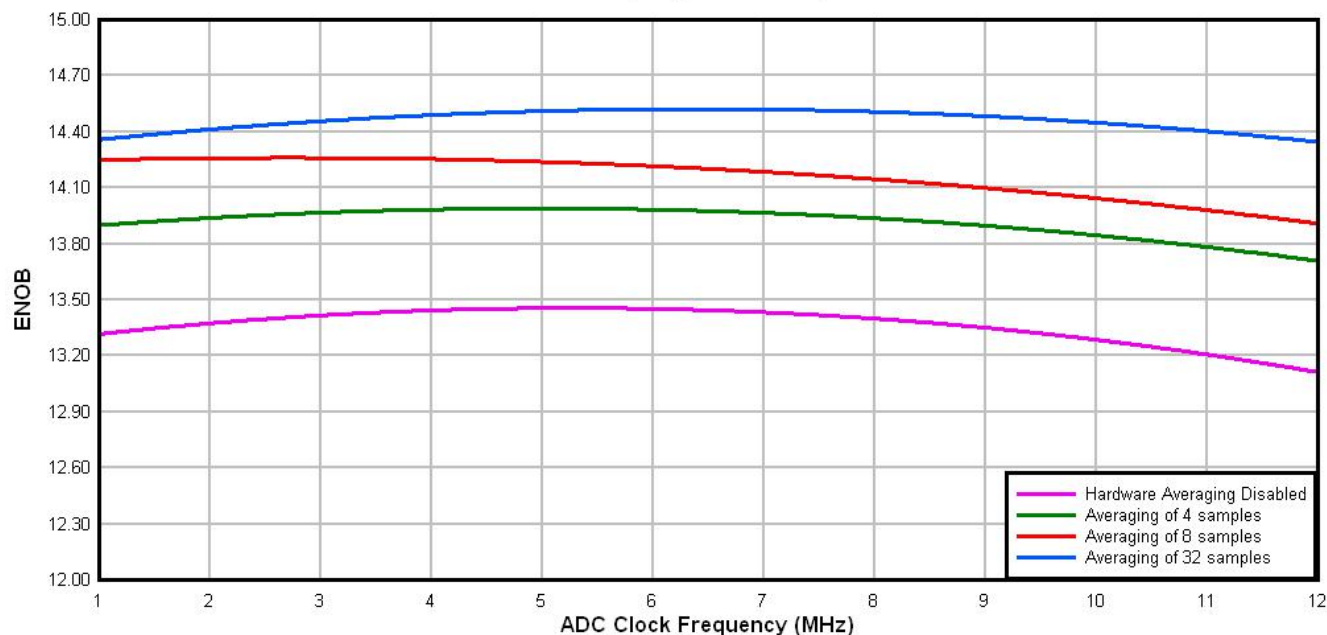
Table continues on the next page...

Table 20. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
E_{IL}	Input leakage error			$I_{IN} \times R_{AS}$		mV	I_{IN} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	—	1.715	—	mV/°C	
V_{TEMP25}	Temp sensor voltage	25 °C	—	719	—	mV	

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume $V_{DDA} = 3.0$ V, Temp = 25°C, $f_{ADCK} = 2.0$ MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and the ADLPC bit (low power). For lowest power operation the ADLPC bit must be set, the HSC bit must be clear with 1 MHz ADC conversion clock speed.
4. $1 \text{ LSB} = (V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.

Typical ADC 16-bit Differential ENOB vs ADC Clock
100Hz, 90% FS Sine Input

**Figure 7. Typical ENOB vs. ADC_CLK for 16-bit differential mode**

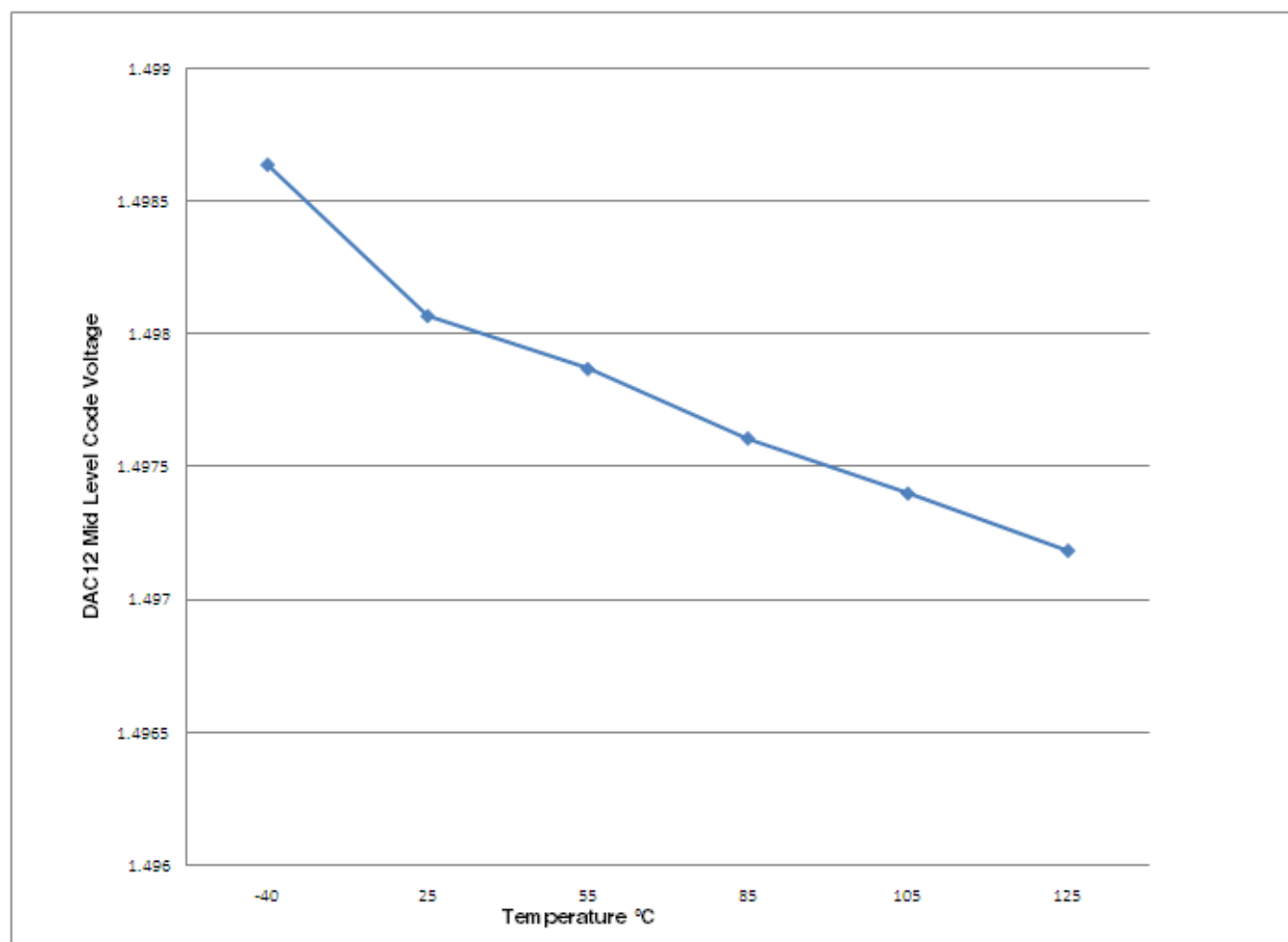


Figure 12. Offset at half scale vs. temperature

6.7 Timers

See General switching specifications.

6.8 Communication interfaces

6.8.1 USB electrical specifications

The USB electricals for the USB On-the-Go module conform to the standards documented by the Universal Serial Bus Implementers Forum. For the most up-to-date standards, visit <http://www.usb.org>.

Table 25. SPI master mode timing on slew rate disabled pads (continued)

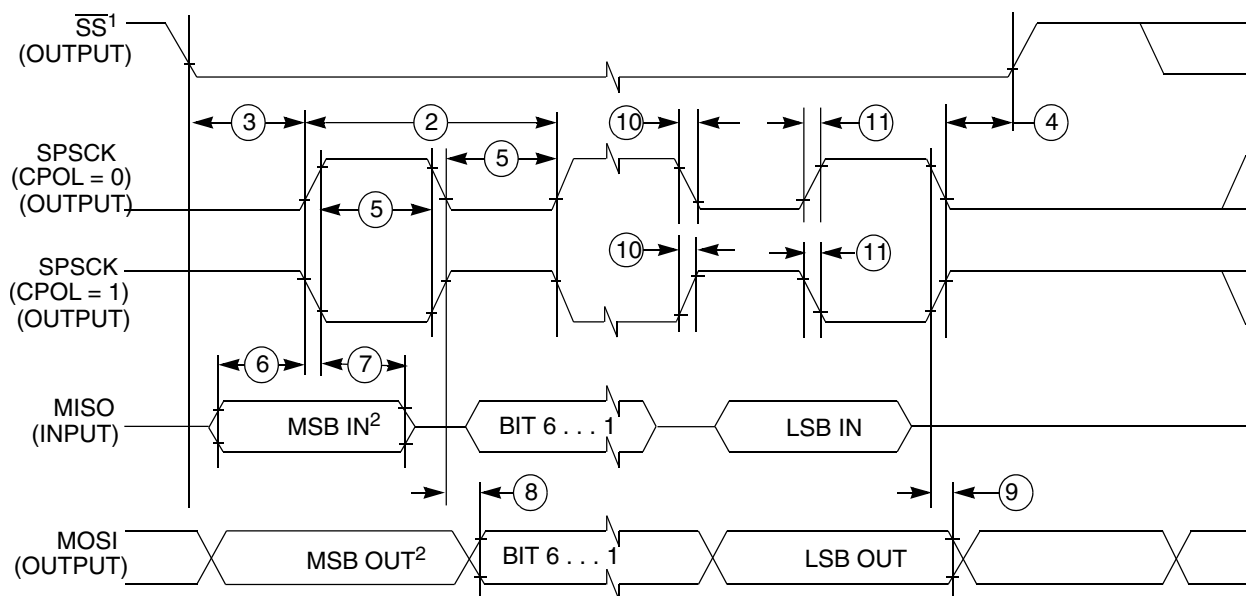
Num.	Symbol	Description	Min.	Max.	Unit	Note
2	t_{SPSCK}	SPSCK period	$2 \times t_{periph}$	$2048 \times t_{periph}$	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	$t_{periph} - 30$	$1024 \times t_{periph}$	ns	—
6	t_{SU}	Data setup time (inputs)	16	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_v	Data valid (after SPSCK edge)	—	10	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	$t_{periph} - 25$	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

- For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
- $t_{periph} = 1/f_{periph}$

Table 26. SPI master mode timing on slew rate enabled pads

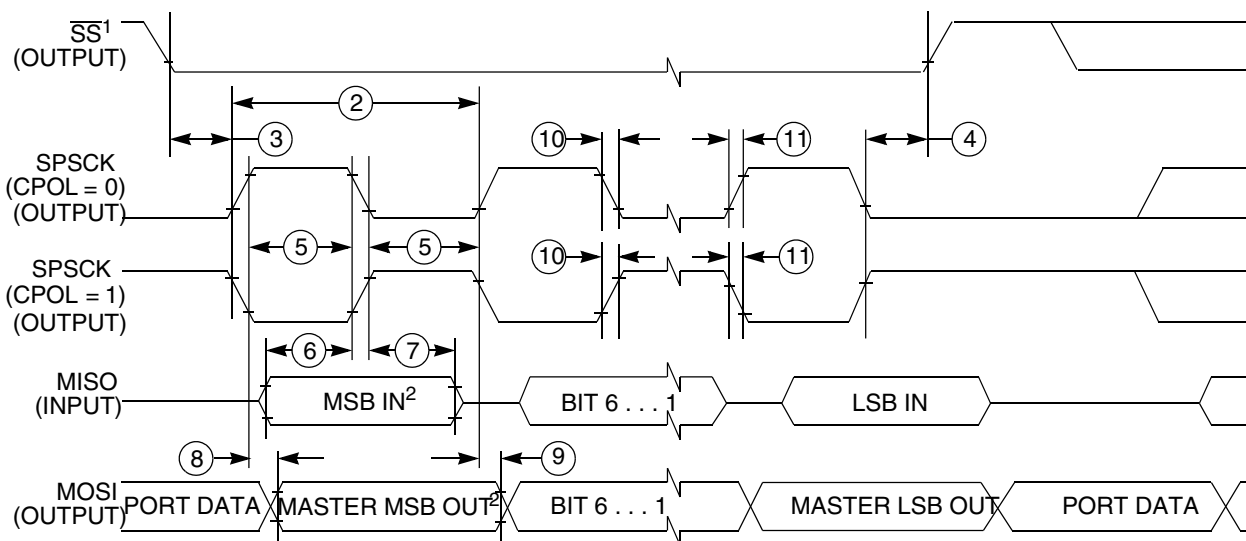
Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	t_{SPSCK}	SPSCK period	$2 \times t_{periph}$	$2048 \times t_{periph}$	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	$t_{periph} - 30$	$1024 \times t_{periph}$	ns	—
6	t_{SU}	Data setup time (inputs)	96	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_v	Data valid (after SPSCK edge)	—	52	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	$t_{periph} - 25$	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	36	ns	—
	t_{FO}	Fall time output				

- For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
- $t_{periph} = 1/f_{periph}$



1. If configured as an output.
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 13. SPI master mode timing (CPHA = 0)



1. If configured as output
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 14. SPI master mode timing (CPHA = 1)

Table 27. SPI slave mode timing on slew rate disabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	t_{SPSCCK}	SPSCCK period	$4 \times t_{periph}$	—	ns	2
3	t_{Lead}	Enable lead time	1	—	t_{periph}	—
4	t_{Lag}	Enable lag time	1	—	t_{periph}	—
5	$t_{WSPSCCK}$	Clock (SPSCCK) high or low time	$t_{periph} - 30$	—	ns	—

Table continues on the next page...

Table 27. SPI slave mode timing on slew rate disabled pads (continued)

Num.	Symbol	Description	Min.	Max.	Unit	Note
6	t_{SU}	Data setup time (inputs)	2	—	ns	—
7	t_{HI}	Data hold time (inputs)	7	—	ns	—
8	t_a	Slave access time	—	t_{periph}	ns	3
9	t_{dis}	Slave MISO disable time	—	t_{periph}	ns	4
10	t_v	Data valid (after SPSCCK edge)	—	22	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	$t_{periph} - 25$	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
2. $t_{periph} = 1/f_{periph}$
3. Time to data active from high-impedance state
4. Hold time to high-impedance state

Table 28. SPI slave mode timing on slew rate enabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	t_{SPSCCK}	SPSCCK period	$4 \times t_{periph}$	—	ns	2
3	t_{Lead}	Enable lead time	1	—	t_{periph}	—
4	t_{Lag}	Enable lag time	1	—	t_{periph}	—
5	$t_{WSPSCCK}$	Clock (SPSCCK) high or low time	$t_{periph} - 30$	—	ns	—
6	t_{SU}	Data setup time (inputs)	2	—	ns	—
7	t_{HI}	Data hold time (inputs)	7	—	ns	—
8	t_a	Slave access time	—	t_{periph}	ns	3
9	t_{dis}	Slave MISO disable time	—	t_{periph}	ns	4
10	t_v	Data valid (after SPSCCK edge)	—	122	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	$t_{periph} - 25$	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	36	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
2. $t_{periph} = 1/f_{periph}$
3. Time to data active from high-impedance state
4. Hold time to high-impedance state

80 LQFP	64 LQFP	48 QFN	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
32	28	—	—	PTA12	DISABLED		PTA12		TPM1_CH0				
33	29	—	—	PTA13	DISABLED		PTA13		TPM1_CH1				
34	—	—	—	PTA14	DISABLED		PTA14	SPI0_PCS0	UART0_TX				
35	—	—	—	PTA15	DISABLED		PTA15	SPI0_SCK	UART0_RX				
36	—	—	—	PTA16	DISABLED		PTA16	SPI0_MOSI			SPI0_MISO		
37	—	—	—	PTA17	DISABLED		PTA17	SPI0_MISO			SPI0_MOSI		
38	30	22	15	VDD	VDD	VDD							
39	31	23	16	VSS	VSS	VSS							
40	32	24	17	PTA18	EXTAL0	EXTAL0	PTA18		UART1_RX	TPM_CLKIN0			
41	33	25	18	PTA19	XTAL0	XTAL0	PTA19		UART1_TX	TPM_CLKIN1		LPTMR0_ ALT1	
42	34	26	19	RESET_b	RESET_b		PTA20						
43	35	27	20	PTB0/ LLWU_P5	ADC0_SE8/ TSIO_CH0	ADC0_SE8/ TSIO_CH0	PTB0/ LLWU_P5	I2C0_SCL	TPM1_CH0				
44	36	28	21	PTB1	ADC0_SE9/ TSIO_CH6	ADC0_SE9/ TSIO_CH6	PTB1	I2C0_SDA	TPM1_CH1				
45	37	29	—	PTB2	ADC0_SE12/ TSIO_CH7	ADC0_SE12/ TSIO_CH7	PTB2	I2C0_SCL	TPM2_CH0				
46	38	30	—	PTB3	ADC0_SE13/ TSIO_CH8	ADC0_SE13/ TSIO_CH8	PTB3	I2C0_SDA	TPM2_CH1				
47	—	—	—	PTB8	DISABLED		PTB8		EXTRG_IN				
48	—	—	—	PTB9	DISABLED		PTB9						
49	—	—	—	PTB10	DISABLED		PTB10	SPI1_PCS0					
50	—	—	—	PTB11	DISABLED		PTB11	SPI1_SCK					
51	39	31	—	PTB16	TSIO_CH9	TSIO_CH9	PTB16	SPI1_MOSI	UART0_RX	TPM_CLKIN0	SPI1_MISO		
52	40	32	—	PTB17	TSIO_CH10	TSIO_CH10	PTB17	SPI1_MISO	UART0_TX	TPM_CLKIN1	SPI1_MOSI		
53	41	—	—	PTB18	TSIO_CH11	TSIO_CH11	PTB18		TPM2_CH0				
54	42	—	—	PTB19	TSIO_CH12	TSIO_CH12	PTB19		TPM2_CH1				
55	43	33	—	PTC0	ADC0_SE14/ TSIO_CH13	ADC0_SE14/ TSIO_CH13	PTC0		EXTRG_IN		CMPO_OUT		
56	44	34	22	PTC1/ LLWU_P6/ RTC_CLKIN	ADC0_SE15/ TSIO_CH14	ADC0_SE15/ TSIO_CH14	PTC1/ LLWU_P6/ RTC_CLKIN	I2C1_SCL		TPM0_CH0			
57	45	35	23	PTC2	ADC0_SE11/ TSIO_CH15	ADC0_SE11/ TSIO_CH15	PTC2	I2C1_SDA		TPM0_CH1			
58	46	36	24	PTC3/ LLWU_P7	DISABLED		PTC3/ LLWU_P7		UART1_RX	TPM0_CH2	CLKOUT		
59	47	—	—	VSS	VSS	VSS							
60	48	—	—	VDD	VDD	VDD							
61	49	37	25	PTC4/ LLWU_P8	DISABLED		PTC4/ LLWU_P8	SPI0_PCS0	UART1_TX	TPM0_CH3			
62	50	38	26	PTC5/ LLWU_P9	DISABLED		PTC5/ LLWU_P9	SPI0_SCK	LPTMR0_ ALT2			CMPO_OUT	
63	51	39	27	PTC6/ LLWU_P10	CMPO_IN0	CMPO_IN0	PTC6/ LLWU_P10	SPI0_MOSI	EXTRG_IN		SPI0_MISO		

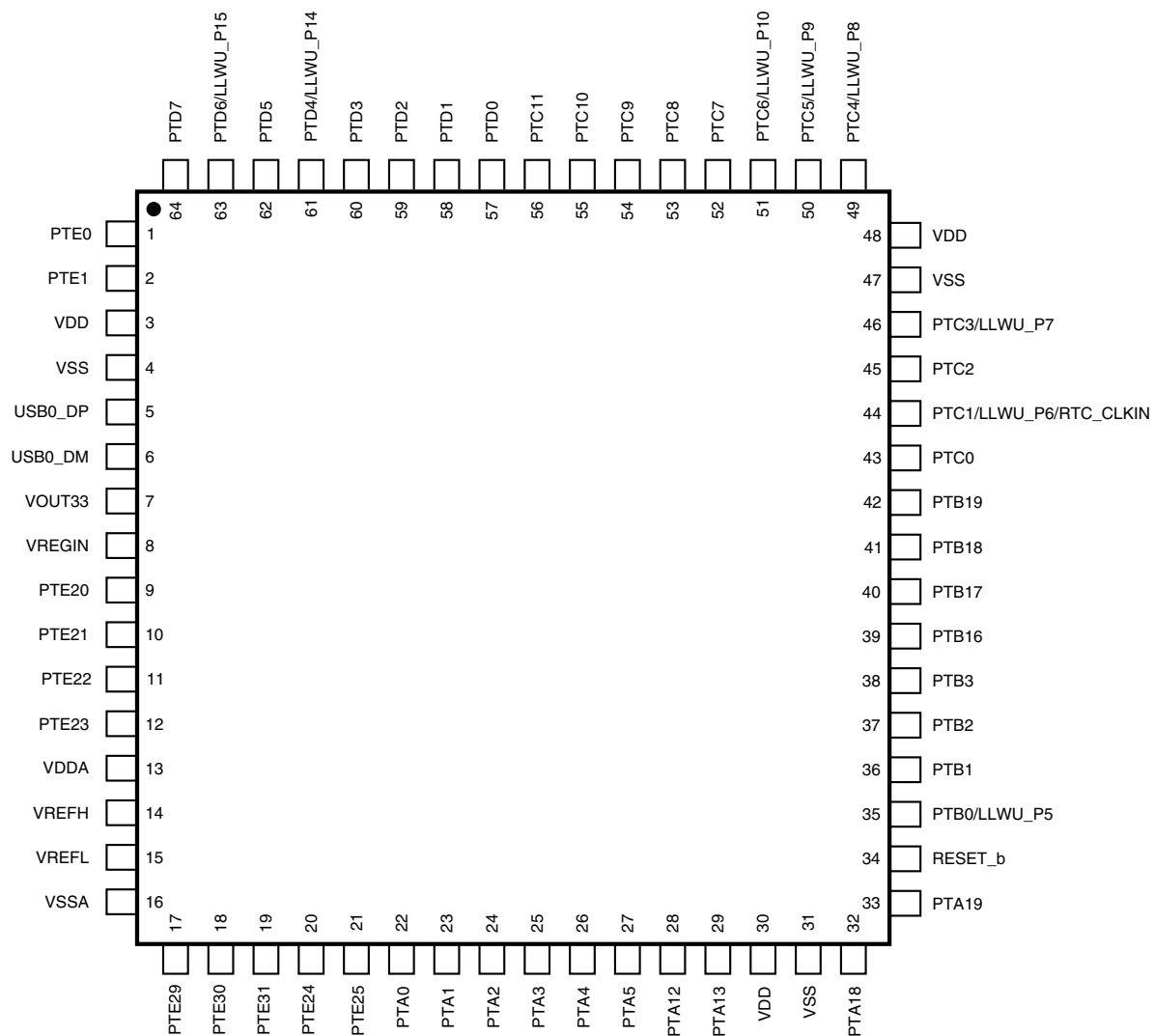


Figure 18. KL25 64-pin LQFP pinout diagram